

Listing of Claims:

This listing of claims replaces all prior versions and listings of claims in the application.

Claims 1-108 (Canceled)

Claim 109 (Currently Amended) A semiconductor device comprising:

a semiconductor element having a surface on which protruding electrodes are formed;
a compression-molded resin layer formed on the surface of the semiconductor element
so as to seal the protruding electrodes except end portions thereof, said end portions protruding a
height from the resin layer; and
external connection protruding electrodes provided to the end portions of the protruding
electrodes that protrude from the resin layer,
said external connection protruding electrodes forming a bump,
said bump having a height larger than said height of said protruding electrode protruding
beyond said resin layer, wherein both a side portion of the resin layer and a side portion of the
semiconductor element are respectively exposed .

Claim 110 (Canceled)

Claim 111 (Currently Amended) A semiconductor device comprising:

a semiconductor element having a surface on which protruding electrodes having convex end portions are formed;

a compression-molded resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except the convex end portions thereof, said convex end portions protruding a height from the resin layer; and

external connection protruding electrodes provided to the convex end portions of the protruding electrodes that protrude from the resin layer,

said external connection protruding electrodes forming a bump,

said bump having a height larger than said height of said protruding electrode protruding beyond said resin layer, wherein both a side portion of the resin layer and a side portion of the semiconductor element are respectively exposed.

Claims 112-114 (Canceled)

Claim 115 (Previously Presented) A semiconductor device comprising:

a semiconductor element having a surface on which electrode pads connected to an internal part of the semiconductor element and protruding electrodes to be connected to an external part are formed;

lead lines each connecting one of the electrode pads and one of the protruding electrodes so that the protruding electrodes and the internal part are connected through the lead lines; and

a resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except end portions thereof,

the protruding electrodes having a core portion and an electrically conductive film formed on a surface of the core portion,

the core portions of the protruding electrodes are directly formed on the lead lines, wherein the core portion comprises an elastic resin,

a part of said protruding electrode sealed by said resin layer and said end portions are covered commonly with said electrically conductive film.

Claim 116 (Previously Presented) The semiconductor device as claimed in claim 115, wherein the elastic resin is polyimide.

Claims 117-118 (Canceled)

Claim 119 (Previously Presented) A semiconductor device comprising:

a semiconductor element having a surface on which electrode pads connected to an internal part of the semiconductor element and protruding electrodes to be connected to an external part are formed;

lead lines each connecting one of the electrode pads and one of the protruding electrodes so that the protruding electrodes and the internal part are connected through the lead lines;

a resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except end portions thereof which protrude from the resin layer; and

external connection protruding electrodes provided to the end portions of the protruding electrodes that protrude from the resin layer,

the protruding electrodes having a core portion and an electrically conductive film formed on a surface of the core portion,

the core portions of the protruding electrodes are directly formed on the lead lines, wherein the core portion comprises an elastic resin, and

a part of said protruding electrode sealed by said resin layer and said end portion are covered commonly with said electrically conductive film.

Claim 120 (Previously Presented) The semiconductor device as claimed in claim 119, wherein the elastic resin is polyimide.

Claims 121-126 (Canceled)

Claim 127 (Previously Presented) A semiconductor device comprising:

a semiconductor element having a surface on which protruding electrodes are formed;
and

a compression-molded resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except end portions thereof,

wherein the compression-molded resin layer and the semiconductor element have surfaces defined by cutting using a dicer.

Claim 128 (Canceled)

Claim 129 (Previously Presented) The semiconductor device as claimed in claim 127, wherein a side surface of the resin layer and a side surface of the semiconductor element are flush with each other.

Claim 130 (Previously Presented) The semiconductor device as claimed in claim 127, wherein end portions of the protruding electrodes protrude from the compression-molded resin layer.

Claim 131 (Previously Presented) A semiconductor device comprising:
a semiconductor element having a surface on which protruding electrodes are formed;
a compression-molded resin layer formed on the surface of the semiconductor element so as to seal the protruding electrodes except end portions thereof; and
external connection protruding electrodes provided to the end portions of the protruding electrodes that protrude from the compression-molded resin layer,
the compression-molded resin layer and the semiconductor element having surfaces defined by cutting using a dicer.

Claim 132 (Canceled)

Claim 133 (Previously Presented) A semiconductor device as claimed in claim 132, wherein a sidewall surface of said first resin layer and a sidewall surface of said second resin layer form a flush surface with said sidewall surface of said semiconductor element.

Claim 134 (Canceled)

Claim 135 (Canceled)